

Abstract of the Disclosure:

Word lines of a semiconductor component are provided with an encapsulation of dielectric material, Spacers of oxide extend alongside at the sidewalls of the word lines. The spacers are
5 subsequently covered together with the word lines with a nitride layer. Borophosphorosilicate glass is introduced between those portions of the nitride layer which respectively belong to a word line and is removed selectively with respect to the nitride using a mask. Contact hole fillings for the
10 electrical connection of the buried bit lines are introduced into the contact holes thus formed.

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